

# N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)		
100	0.040 at V <sub>GS</sub> = 10 V	6.4	23 nC		
100	0.047 at V <sub>GS</sub> = 8 V	5.5	23110		

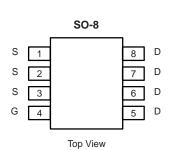
### **FEATURES**

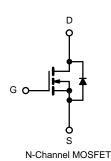
- $\bullet \quad \text{Extremely Low } \mathsf{Q}_{\mathsf{gd}} \text{ for Switching Losses } \\$
- 100 % R<sub>g</sub> Tested
- 100 % Avalanche Tested
- Compliant to RoHS Directive 2002/95/EC



#### **APPLICATIONS**

· Primary Side Switch





Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		$V_{DS}$	100	V	
Gate-Source Voltage		$V_{GS}$	± 20		
	T <sub>C</sub> = 25 °C		6.4		
Continuous Drain Current (T. 150 °C)	T <sub>C</sub> = 70 °C	1 1	5.1		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	5.5 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	1	4.5 <sup>b, c</sup>	Α	
Pulsed Drain Current		I <sub>DM</sub>	50		
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C		4.5		
	T <sub>A</sub> = 25 °C	I <sub>S</sub>	2.6 <sup>b, c</sup>		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	20		
Single Pulse Avalanche Energy	L = 0.111111	E <sub>AS</sub>	20	mJ	
	T <sub>C</sub> = 25 °C		5.9		
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	]	3.8	W	
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.1 <sup>b, c</sup>	VV	
	T <sub>A</sub> = 70 °C	1	2 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stq</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 10 s	R <sub>thJA</sub>	33	40	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	17	21	7 0/1/		

#### Notes:

- a. Based on  $T_C = 25$  °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under steady state conditions is 80 °C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static			•				
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	$\Delta V_{DS}/T_{J}$		172		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	I <sub>D</sub> = 250 μA		- 10		lliv/°C	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_{D} = 250 \mu\text{A}$	2.5		4.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zone Onto Valta na Busin Occurs at		$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
Dunin Course On Chata Basistanas	i ' i	$V_{GS} = 10 \text{ V, } I_{D} = 5 \text{ A}$		0.036	0.040	0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 8 V, I <sub>D</sub> = 5 A		0.0375	0.047	Ω	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 5 \text{ A}$		23		S	
Dynamic <sup>b</sup>		-					
Input Capacitance	C <sub>iss</sub>			1735		pF	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		160			
Reverse Transfer Capacitance	C <sub>rss</sub>			37			
Total Cata Charga		V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A		28.5	43	nC	
Total Gate Charge	Qg			23	35		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 75 \text{ V}, V_{GS} = 8 \text{ V}, I_{D} = 5 \text{ A}$		8			
Gate-Drain Charge	Q <sub>qd</sub>			6.5			
Gate Resistance	R <sub>a</sub>	f = 1 MHz		0.85	1.3	Ω	
Turn-on Delay Time	t <sub>d(on)</sub>			14	21		
Rise Time	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, R_L = 10 \Omega$		12	18		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 5 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		22	33	1	
Fall Time	t <sub>f</sub>			6	10		
Turn-On Delay Time	t <sub>d(on)</sub>			16	24	ns -	
Rise Time	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, R_L = 10 \Omega$		12	18		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 5 \text{ A}, V_{GEN} = 8 \text{ V}, R_g = 1 \Omega$		20	30		
Fall Time	t <sub>f</sub>	_		7	12	1	
<b>Drain-Source Body Diode Characteristic</b>	s						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			7.7	^	
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				50	A	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 2.6 A		0.77	1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	-		63	95	ns	
Body Diode Reverse Recovery Charge	Body Diode Reverse Recovery Charge 0			110	165	nC	
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = 5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$		49		1	
Reverse Recovery Rise Time	t <sub>b</sub>			14		ns	

#### Notes:

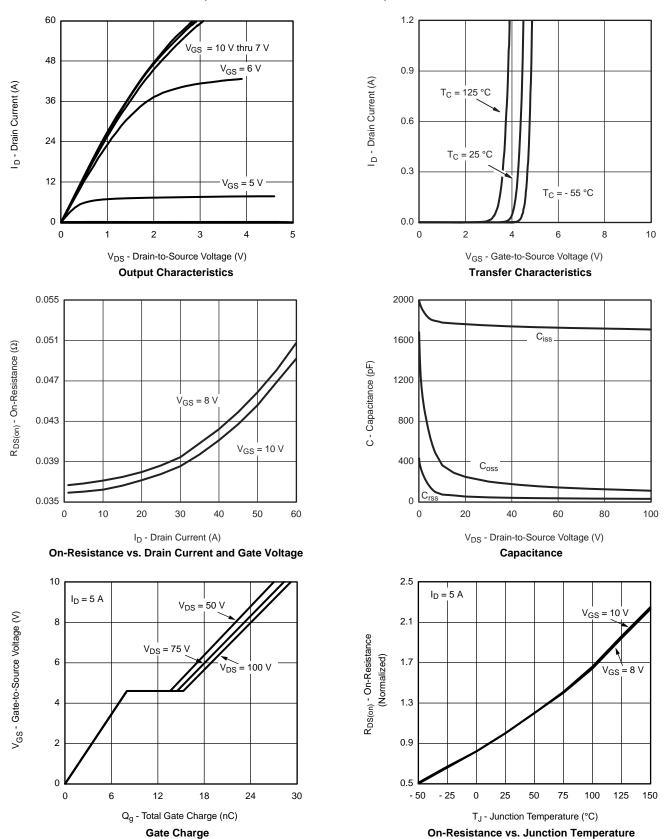
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$ 

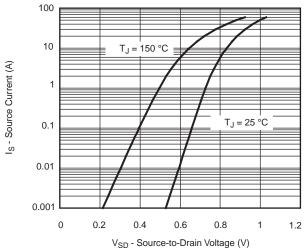
a. Guaranteed by design, not subject to production testing.

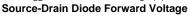


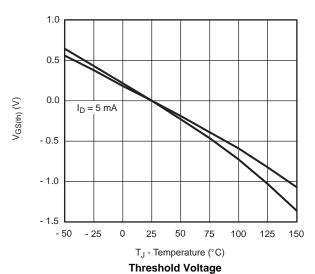




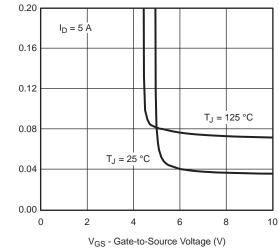




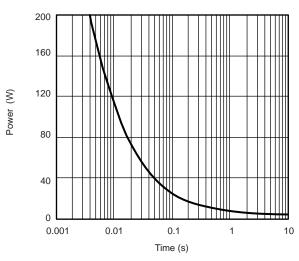




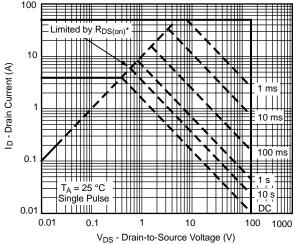
 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - Drain-to-Source On-Resistance  $(\Omega)$ 



On-Resistance vs. Gate-to-Source Voltage

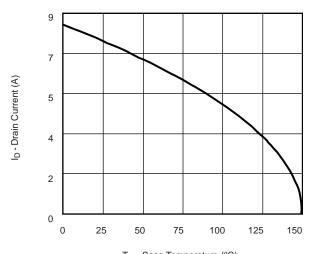


Single Pulse Power, Junction-to-Ambient

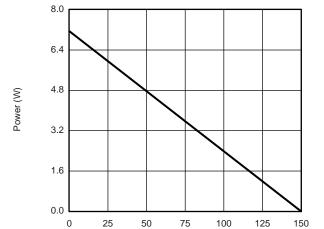


\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

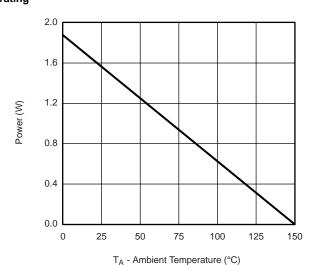
Safe Operating Area, Junction-to-Ambient



T<sub>C</sub> - Case Temperature (°C) **Current Derating\*** 



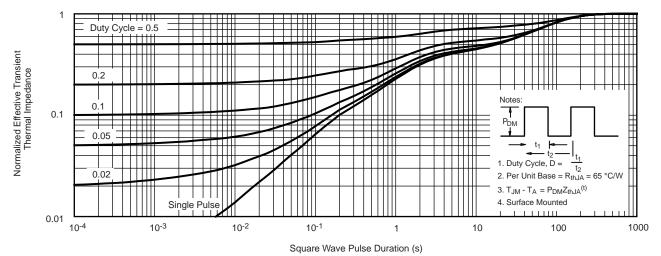




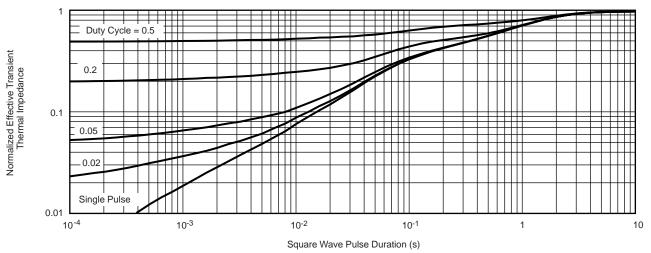
Power, Junction-to-Ambient

<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



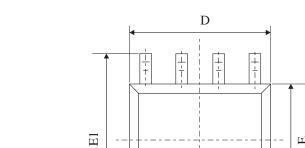
Normalized Thermal Transient Impedance, Junction-to-Foot



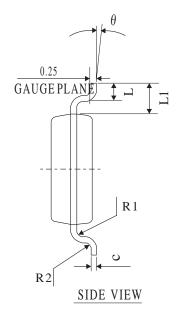
**Din-Tek** 

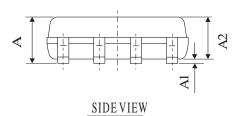
SEMICONDUCTOR

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TOP VIEW

COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX		
A	1.30	1.60	1.85		
A1	0.03	0.15	0.28		
A2	1.20	1.45	1.70		
b	0.26	0.40	0.54		
С	0.132	0.203	0.273		
D	4.50	4.90	5.30		
Е	3.50	3.00	4.30		
E1	5.50	6.00	6.50		
L	0.30	0.70	1.10		
θ	2°	4°	6°		
L1	1.04REF				
e	1.27BSC				
R1	0.07TYP				
R2	0.07TYP				





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